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U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU		EXAMINE	R
10050322	01/15/2002	438	313	2812			Barreca
**APPLICANT		ng Huan; 430	Tao Hun-Jan;		· ·		Daneca
	PPLICATIONS VE	RIFIED:			a de la compansión		
PG-PUB DO N Foreign priority clai	OT PUBLISH 🖵		RESCIN	1D 🗂	ATTO	DRNEY DOCKE	T NO
35 USC 119 condit		⊐ yes			1	00-613	110
TITLE: Bi-layer	photoresist dry de	velopmer	nt and reactive	ion etch			M-PTO-436L(Rev. 12-94)
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	Foreign priority 35 USC 119 co. Verified and Ac		⊐ yes ⊉ no ⊐ yes ⊉ no s intials		ATTORNEY DC 67,200-613	OCKET NO			
	TITLE : Bi-la	yer photoresist dry	development and	reactive ion etch n	nethod U.S.DEPT, OF COMM./I	PAT.6 TM-PTO-436L	(Rev. 12-94)		
7	NOTICE OF ALL	OWANCE MAILED	1		CLA	CLAIMS ALLOWED			
			Assistant Ex	aminer	Total Claims	Prin 0.6	t Claim for		
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	Amount Due	Date Paid	7		Sheets Drwg.	Figs.Drwg.	Print Fig.		
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	TERMINAL DISCLAMER		PREPAR	LED FOR ISSUE	Application	Application Examiner			
			WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.						
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